

**GaAs SP4T Switch, Absorptive, Single Supply
DC - 3.0 GHz**

**MASWCC0009
V5**

Features

- Typical Isolation: 35 dB (2.0 GHz)
- Typical Insertion Loss: 1.2 dB (2.0 GHz)
- Integral ASIC/CMOS Driver
- 50 Ohm Nominal Impedance
- Low DC Power Consumption
- Test Boards Available
- Lead-Free QSOP-24 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free “Green” Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of SW65-0440

Description

M/A-COM's MASWCC0009 is a GaAs MMIC absorptive SP4T switch with an integral silicon ASIC driver. This device is in a 24-lead plastic package. This switch offers excellent broadband performance and repeatability from DC to 3 GHz, while maintaining low DC power dissipation. The MASWCC0009 is ideally suited for wireless infrastructure applications.

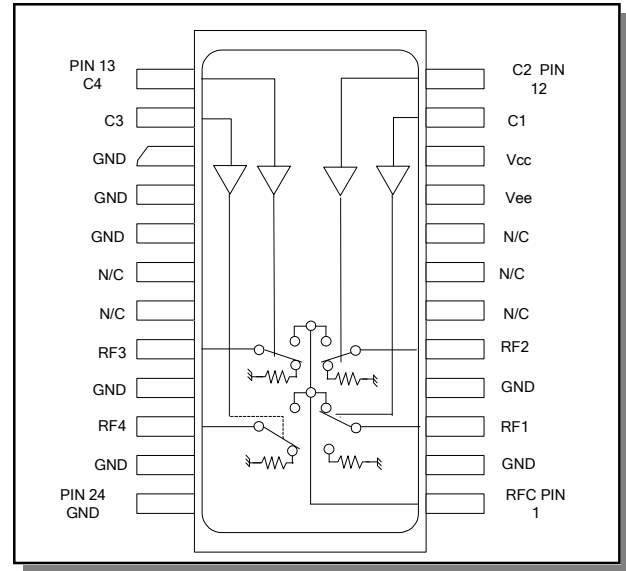
Ordering Information

Part Number	Package
MASWCC0009	Bulk Packaging
MASWCC0009TR	1000 piece reel
MASWCC0009-TB	Sample Test Board

Note: Reference Application Note M513 for reel size information.

Note: Die quantity varies.

Functional Schematic



Pin Configuration

Pin No.	Function	Pin No.	Function
1	RFC	13	C4
2	GND	14	C3
3	RF1	15	GND
4	GND	16	GND
5	RF2	17	GND
6	NC	18	NC
7	NC	19	NC
8	NC	20	RF3
9	V _{EE}	21	GND
10	V _{CC}	22	RF4
11	C1	23	GND
12	C2	24	GND

NC = No Connection

The exposed pad centered on the package bottom must be connected to RF and DC ground. (For MLF Packages)

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

**GaAs SP4T Switch, Absorptive, Single Supply
DC - 3.0 GHz**

**MASWCC0009
V5**

Electrical Specifications: T_A = 25°C

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss	DC - 2.0 GHz	dB	—	1.2	1.8
	DC - 3.0 GHz	dB	—	1.3	2.5
Isolation	DC - 2.0 GHz	dB	32	35	—
	DC - 3.0 GHz	dB	25	29	—
VSWR	RF1-RF4 On	DC - 3.0 GHz	—	1.2:1	1.6:1
	RF1- RF4 Off	DC - 3.0 GHz	—	1.4:1	1.8:1
	RFC	DC - 2.0 GHz	—	1.2:1	1.5:1
	RFC	DC - 3.0 GHz	—	1.6:1	2.2:1
Switching Speed ¹	T _{rise} T _{fall}	10%/90%, 90%/10%	—	15	50
	T _{on} T _{off}	50% TTL to 90%/10% RF	—	50	150
	Transients	In-band (peak to peak)	—	50	150
1 dB Compression	.05 GHz	dBm	—	+20	—
	.5 - 3.0 GHz	dBm	—	+27	—
Input IP ₃	Two tone inputs 0.05 GHz	dBm	—	+35	—
	up to +5 dBm 0.5 - 3.0 GHz	dBm	—	+46	—
V _{CC}	—	V	+4.5	+5.0	+5.5
V _{EE}	—	V	-8.0	-5.0	-4.75
V _{IL} V _{IH}	LOW-level input voltage	V	0.0	—	0.8
	HIGH-level input voltage	V	2.0	—	5.0
I _{in} (Input Leakage Current)	V _{in} = V _{CC} or GND	uA	-1.0	—	1.0
I _{cc} (Quiescent Supply Current)	V _{cntrl} = V _{CC} or GND	uA	—	250	400
ΔI _{cc} (Additional Supply Current Per TTL Input Pin)	V _{CC} = Max, V _{cntrl} = V _{CC} - 2.1 V	mA	—	—	1.0
I _{EE}	V _{EE} min to max, V _{in} = V _{IL} or V _{IH}	mA	-1.0	-0.2	—

1. Decoupling capacitors (.1 μF) are required on the power supply lines.

Absolute Maximum Ratings ^{2,3,4}

Parameter	Absolute Maximum
Max. Input Power 0.05 GHz 0.5 - 3.0 GHz	+27 dBm +34 dBm
V _{CC}	-0.5V ≤ V _{CC} ≤ +7.0V
V _{EE}	-8.5V ≤ V _{EE} ≤ +0.5V
V _{CC} - V _{EE}	-0.5V ≤ V _{CC} - V _{EE} ≤ 14.5V
V _{in} ⁵	-0.5V ≤ V _{in} ≤ V _{CC} + 0.5V
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +125°C

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- When the RF input is applied to the terminated port, the absolute maximum power is +30 dBm.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

Truth Table (Switch)

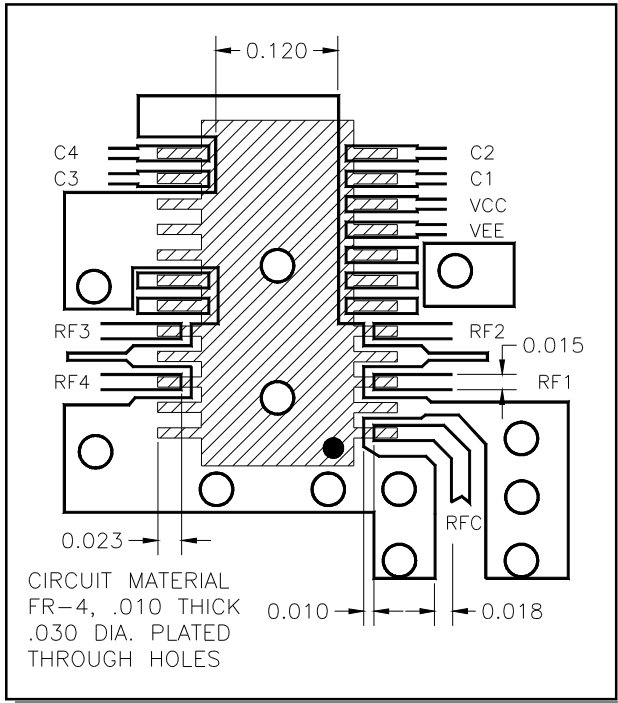
TTL				RF Common To:			
C1	C2	C3	C4	RF1	RF2	RF3	RF4
1	0	0	0	On	Off	Off	Off
0	1	0	0	Off	On	Off	Off
0	0	1	0	Off	Off	On	Off
0	0	0	1	Off	Off	Off	On

0 = TTL Low; 1 = TTL High

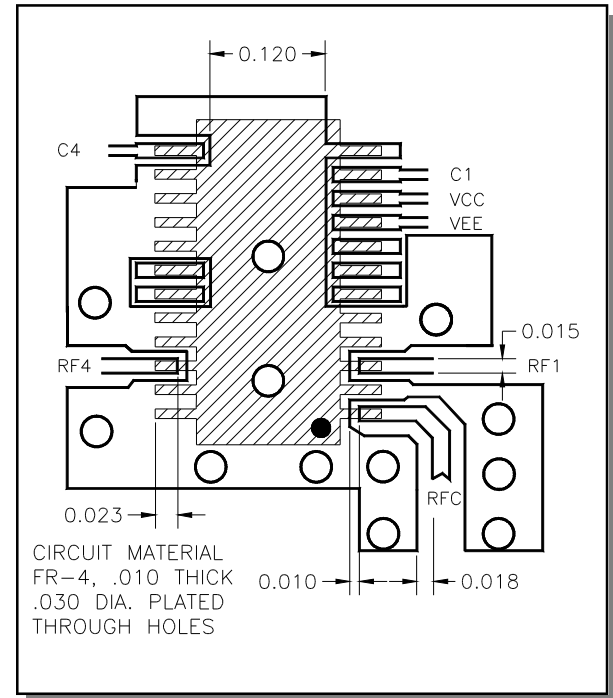
**GaAs SP4T Switch, Absorptive, Single Supply
DC - 3.0 GHz**

**MASWCC0009
V5**

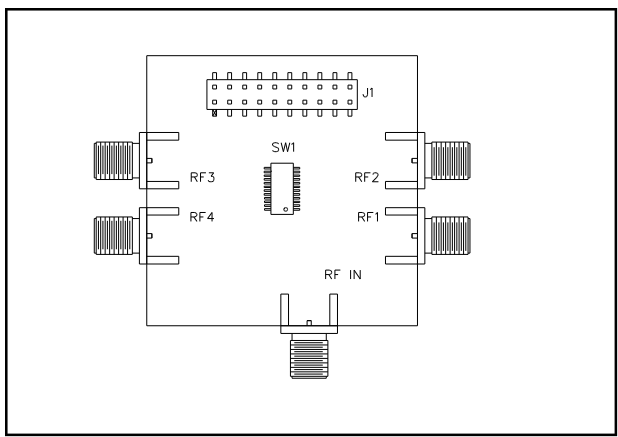
Recommended PCB Layout—SP4T



Recommended PCB Layout—SP2T



Evaluation Board - SW65-0440-TB



Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

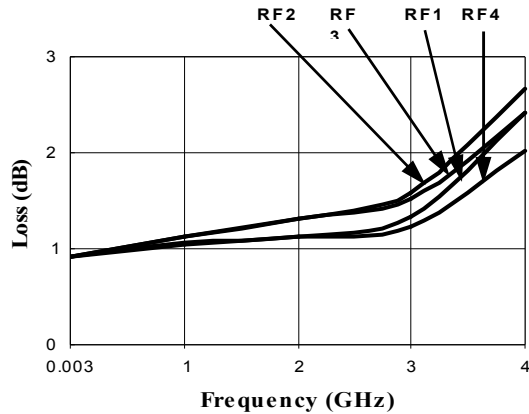
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

**GaAs SP4T Switch, Absorptive, Single Supply
DC - 3.0 GHz**

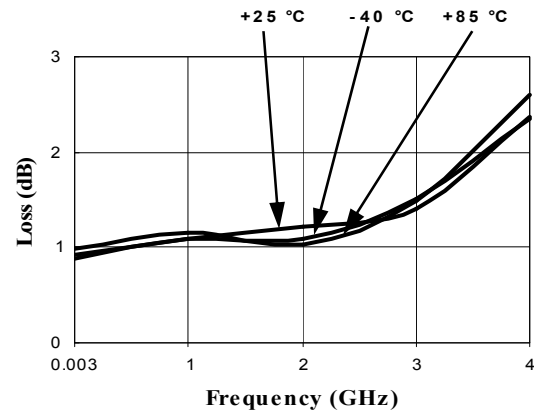
**MASWCC0009
V5**

Typical Performance Curves

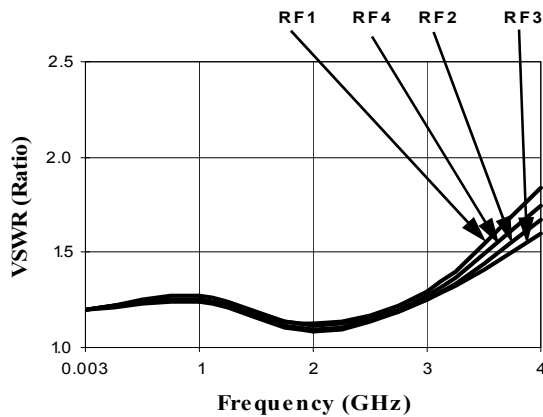
Insertion Loss (dB) @ +25°C



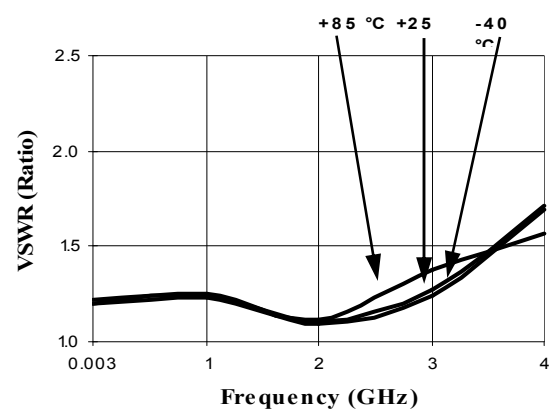
Loss Variation Over Temp. (dB)



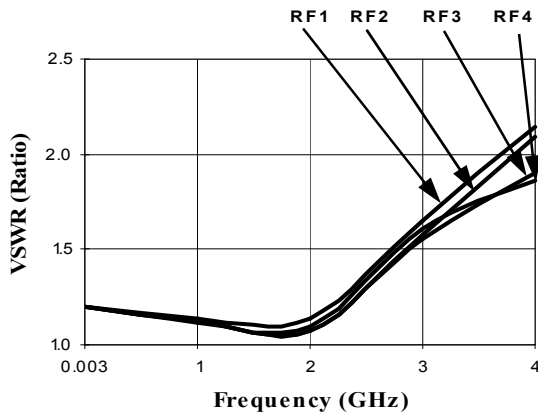
RF1 - RF4 On VSWR @ +25°C



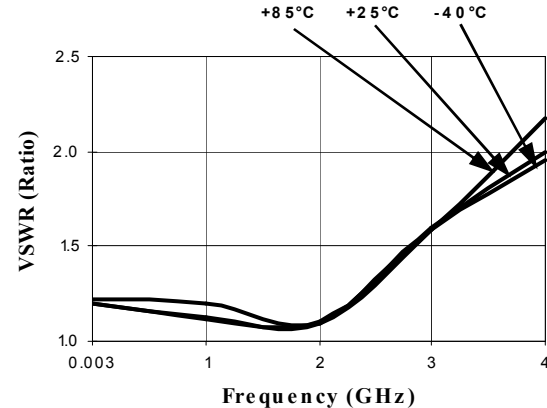
RF1 - RF4 On VSWR Temp. Variation



RFC On VSWR @ +25°C

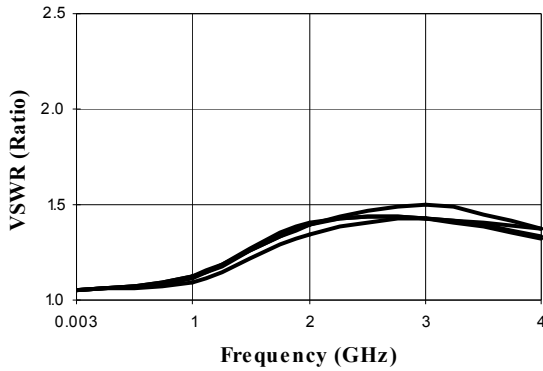


RFC On VSWR Temp. Variation

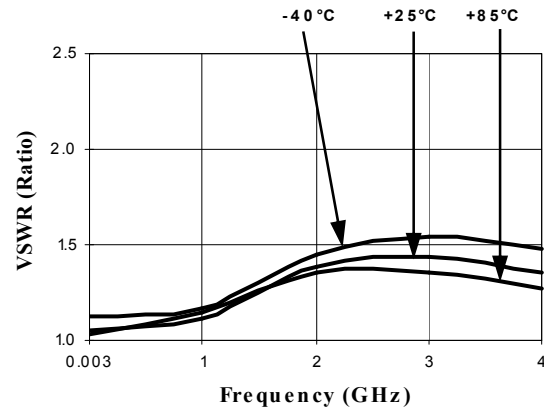


Typical Performance Curves

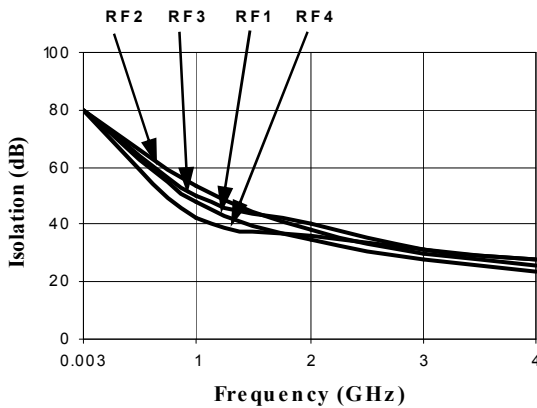
RF1 - RF4 Off VSWR @ +25°C



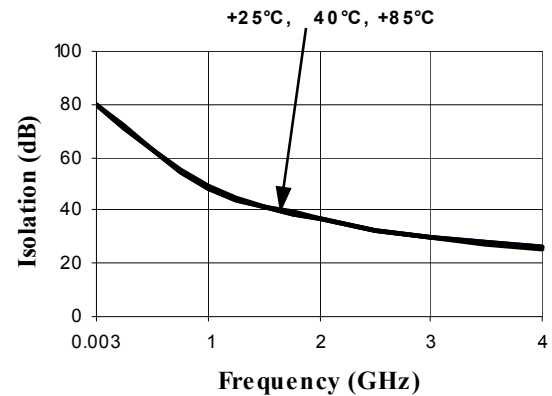
RF1 - RF4 Off VSWR Temp. Variation



Isolation (dB) @ +25°C



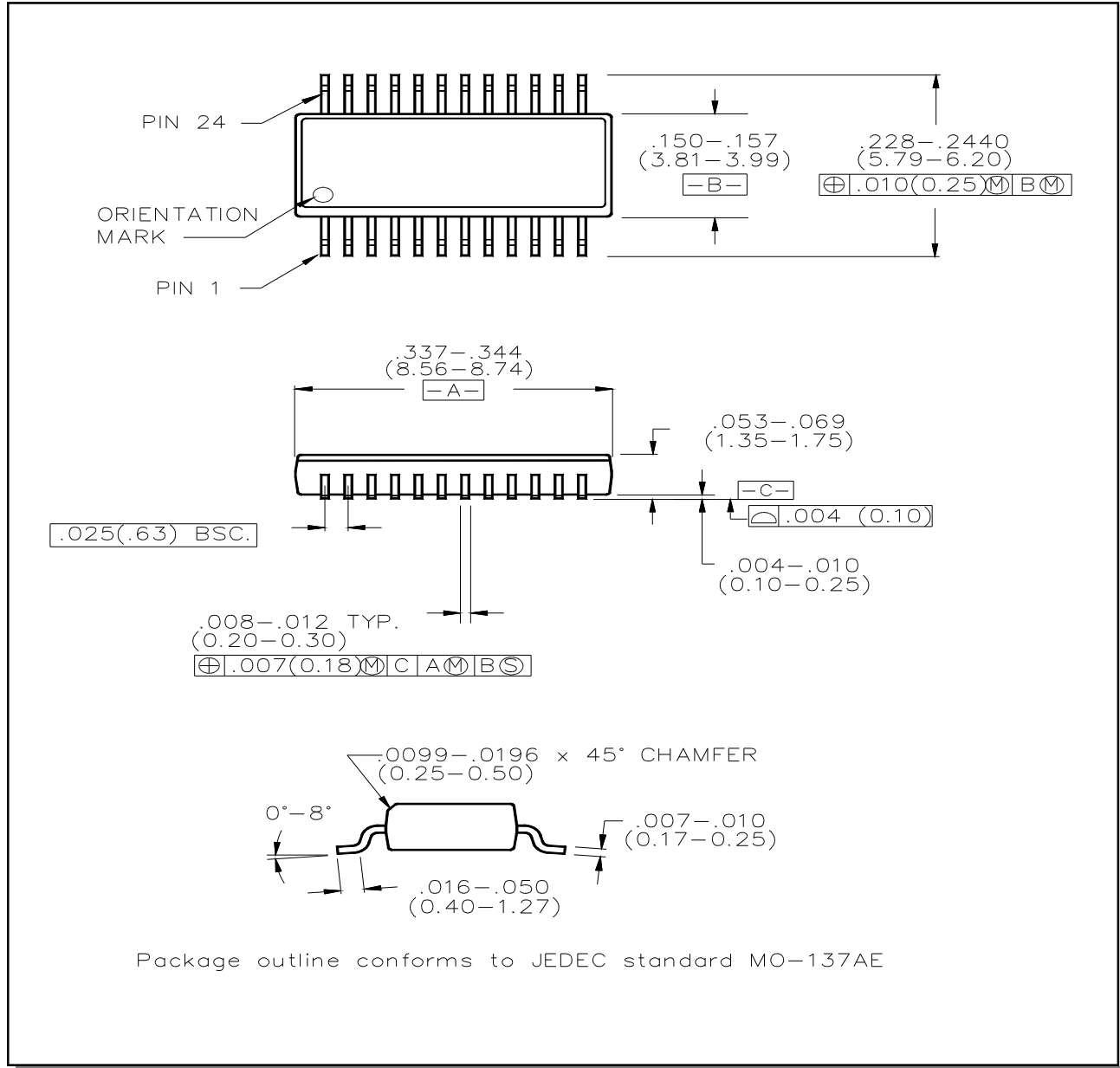
Isolation Temp. Variation (dB)



**GaAs SP4T Switch, Absorptive, Single Supply
DC - 3.0 GHz**

**MASWCC0009
V5**

Lead-Free, QSOP-24[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.